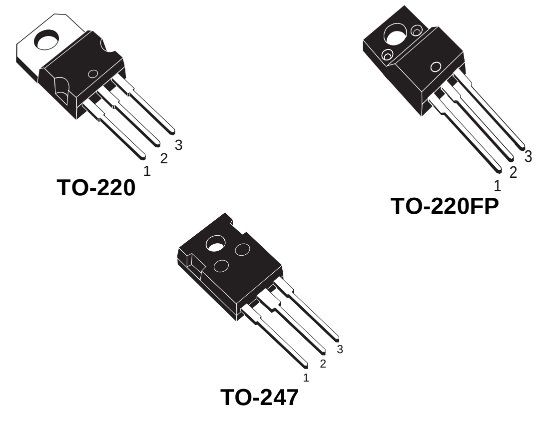
STP8NK80Z - STP8NK80ZFP
STW8NK80Z

N-CHANNEL 800V - 1.3Ω - 6.2A TO-220/TO-220FP/TO-247
Zener-Protected SuperMESH™Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D	P_W
STP8NK80Z	800 V	< 1.5 Ω	6.2 A	140 W
STP8NK80ZFP	800 V	< 1.5 Ω	6.2 A	30 W
STW8NK80Z	800 V	< 1.5 Ω	6.2 A	140 W

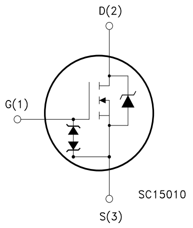
- TYPICAL R_{DS}(on) = 1.3 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY



DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTORS AND PFC
- LIGHTING

ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP8NK80Z	P8NK80Z	TO-220	TUBE
STP8NK80ZFP	P8NK80ZFP	TO-220FP	TUBE
STW8NK80Z	W8NK80Z	TO-247	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP8NK80Z - STW8NK80Z	STP8NK80ZFP	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	800		V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	800		V
V_{GS}	Gate- source Voltage	± 30		V
I_D	Drain Current (continuous) at T_C = 25°C	6.2	6.2 (*)	A
I_D	Drain Current (continuous) at T_C = 100°C	3.9	3.9 (*)	A
I_{DM} (•)	Drain Current (pulsed)	24.8	24.8 (*)	A
P_{TOT}	Total Dissipation at T_C = 25°C	140	30	W
	Derating Factor	1.12	0.24	W/°C
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5 KΩ)	4000		V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5		V/ns
V_{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150		°C

(●) Pulse width limited by safe operating area
(1) I_{SD} ≤6.2A, di/dt ≤200 A/µs, $V_{DD} \le V_{(BR)DSS}$, $T_j \le T_{JMAX}$.
(*) Limited only by maximum temperature allowed

THERMAL DATA

		TO-220	TO-220FP	TO-247	
Rthj-case	Thermal Resistance Junction-case Max	0.89	4.2	0.89	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5		50	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300			°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	6.2	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25°C, $I_D = I_{AR}$, V_{DD} = 50 V)	300	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1 mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device’s ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device’s integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	800			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 3.1 A		1.3	1.5	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} = 15 V, I_D = 3.1 A		5.2		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0		1320 143 27		pF pF pF
$C_{oss\ eq.}$ (3)	Equivalent Output Capacitance	V_{GS} = 0, V_{DS} = 640 V		58		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 400 V, I_D = 3.1 A R_G = 4.7Ω, V_{GS} = 10 V (Resistive Load see, Figure 3)		17 30		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 640 V, I_D = 6.2 A, V_{GS} = 10 V		46 8.5 25		nC nC nC

SWITCHING OFF

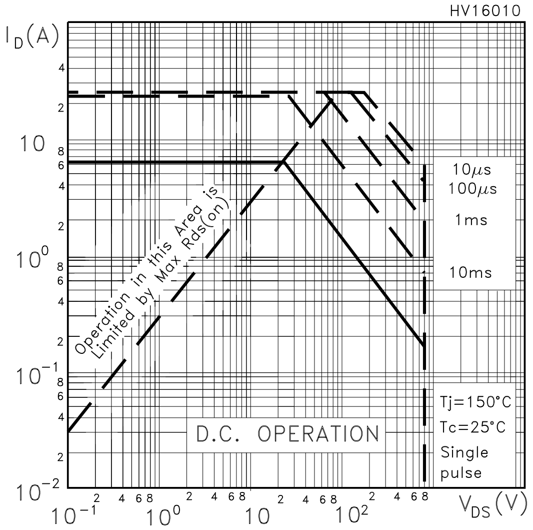
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 400 V, I_D = 3.1 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		48 28		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 640V, I_D = 6.2 A, R_G = 4.7Ω, V_{GS} = 10 V (Inductive Load see, Figure 5)		9 9 18		ns ns ns

SOURCE DRAIN DIODE

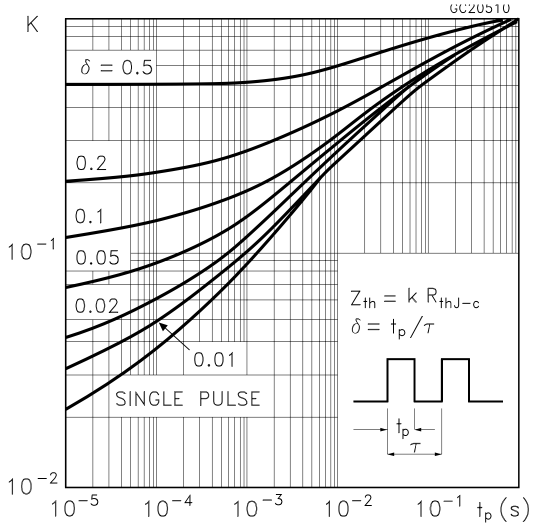
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				6.2 24.8	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 6.2 A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 6.2 A, di/dt = 100 A/µs V_{DD} = 50 V, T_j = 150°C (see test circuit, Figure 5)		460 2990 13		ns nC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

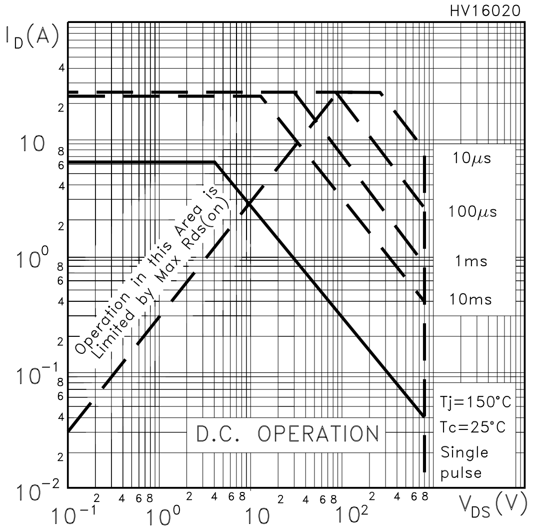
Safe Operating Area For TO-220



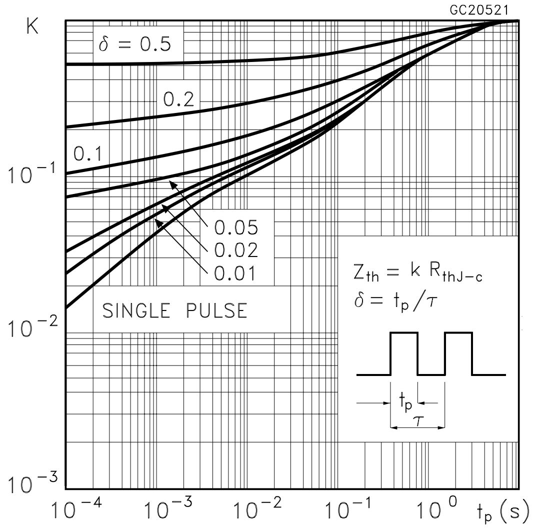
Thermal Impedance For TO-220



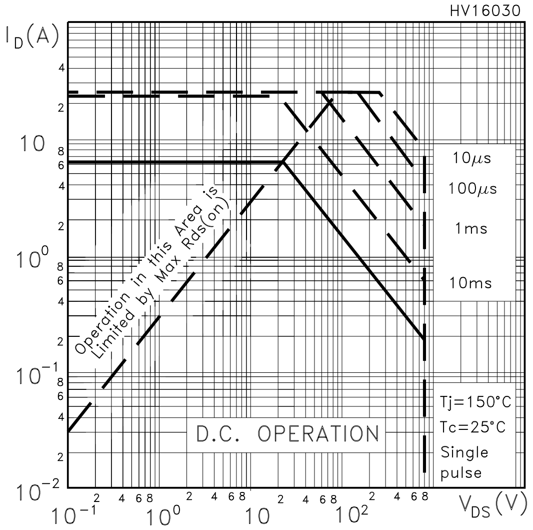
Safe Operating Area For TO-220FP



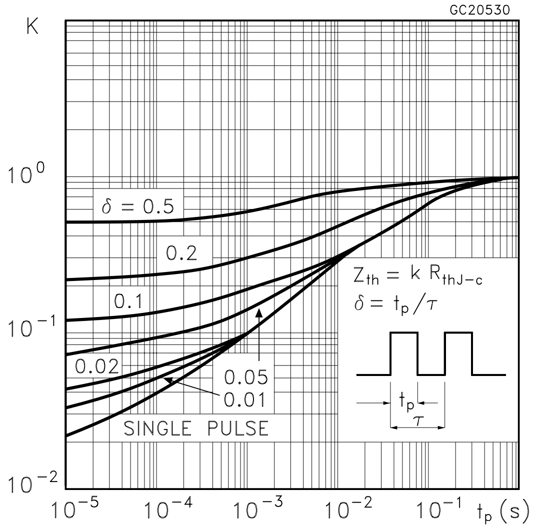
Thermal Impedance For TO-220FP



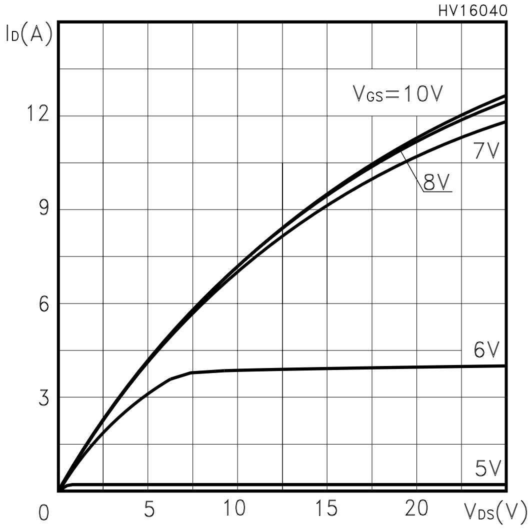
Safe Operating Area For TO-247



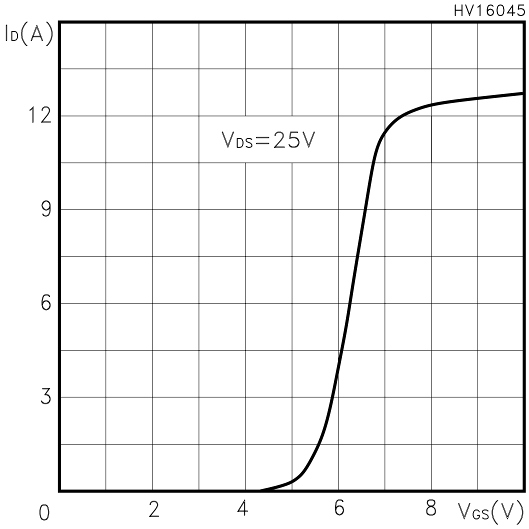
Thermal Impedance For TO-247



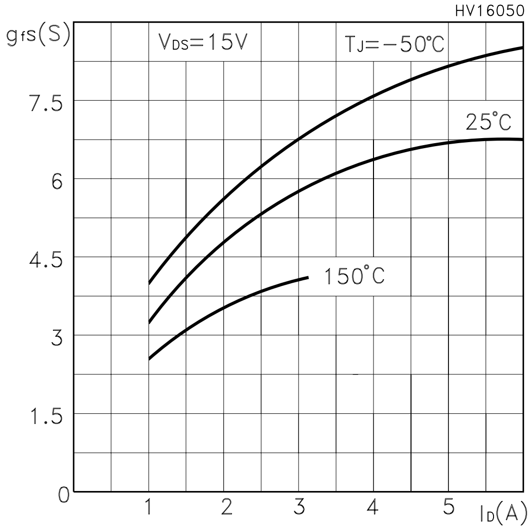
Output Characteristics



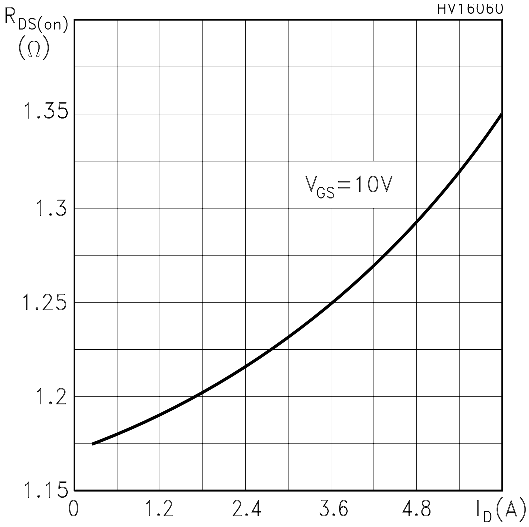
Transfer Characteristics



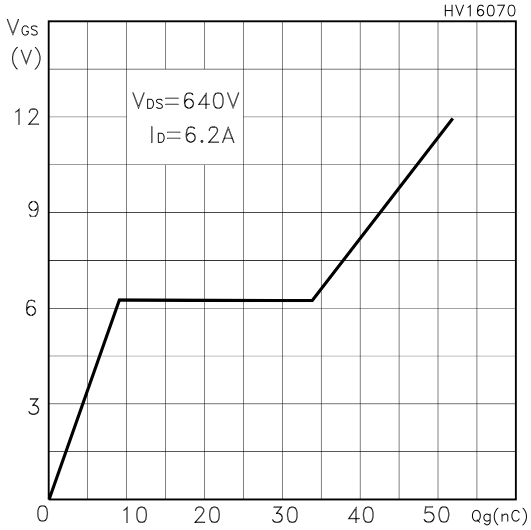
Transconductance



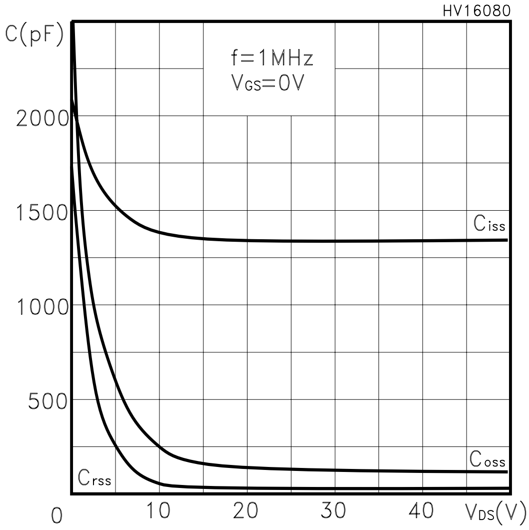
Static Drain-source On Resistance



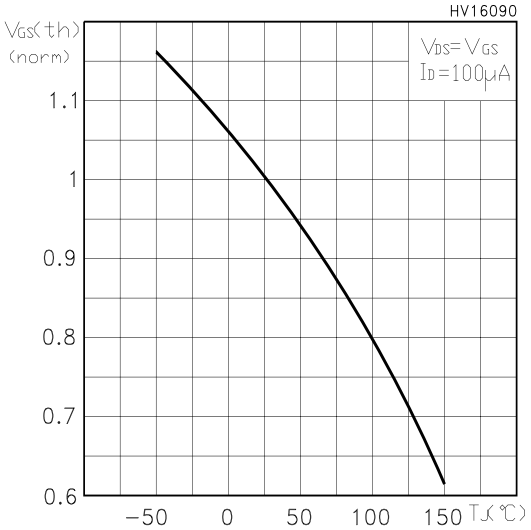
Gate Charge vs Gate-source Voltage



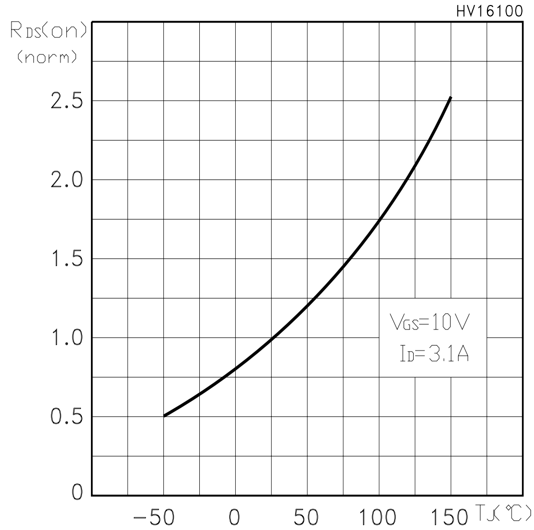
Capacitance Variations



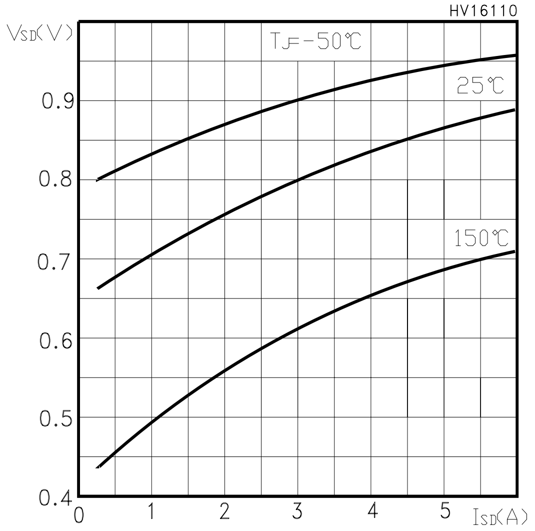
Normalized Gate Threshold Voltage vs Temp.



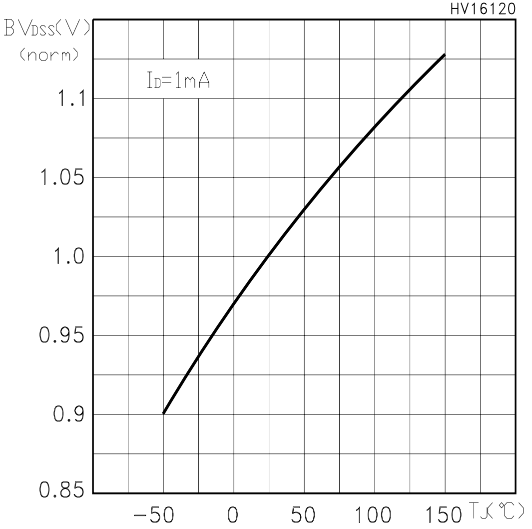
Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature



Maximum Avalanche Energy vs Temperature

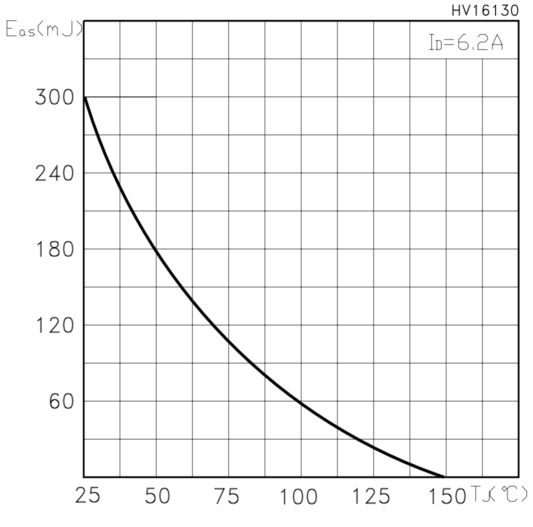


Fig. 1: Unclamped Inductive Load Test Circuit

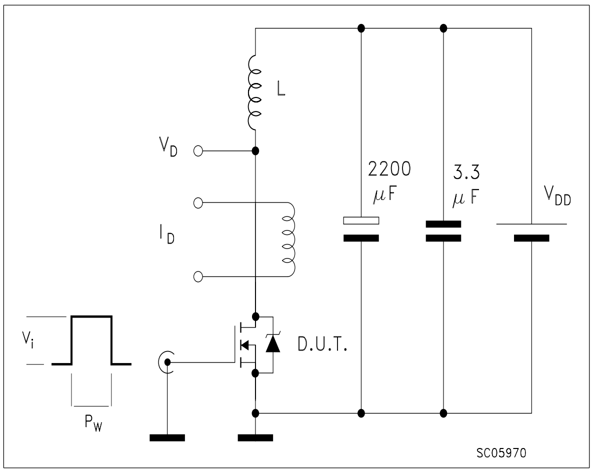


Fig. 2: Unclamped Inductive Waveform

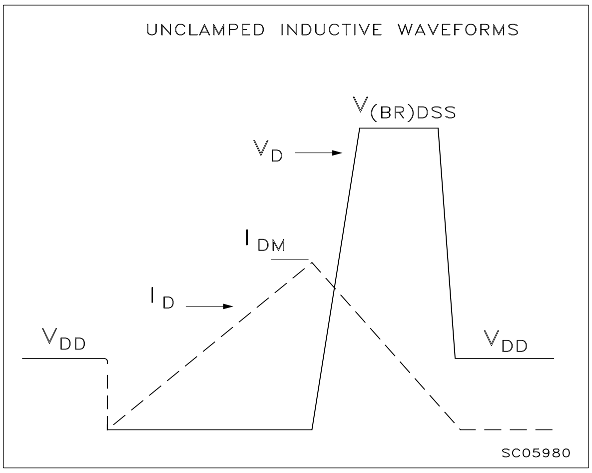


Fig. 3: Switching Times Test Circuit For Resistive Load

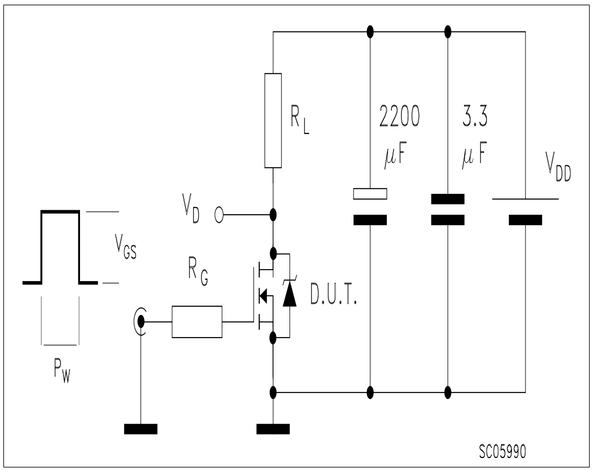


Fig. 4: Gate Charge test Circuit

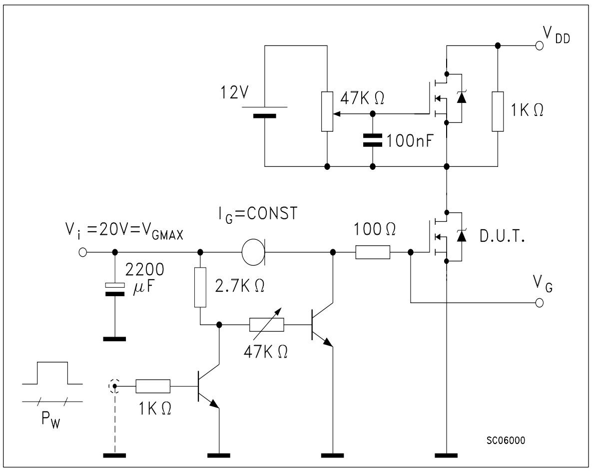
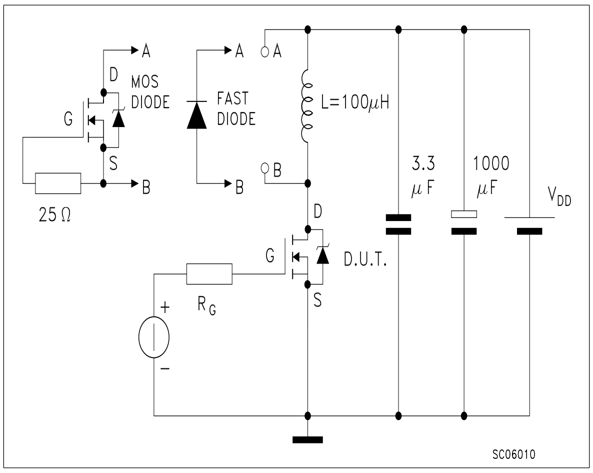
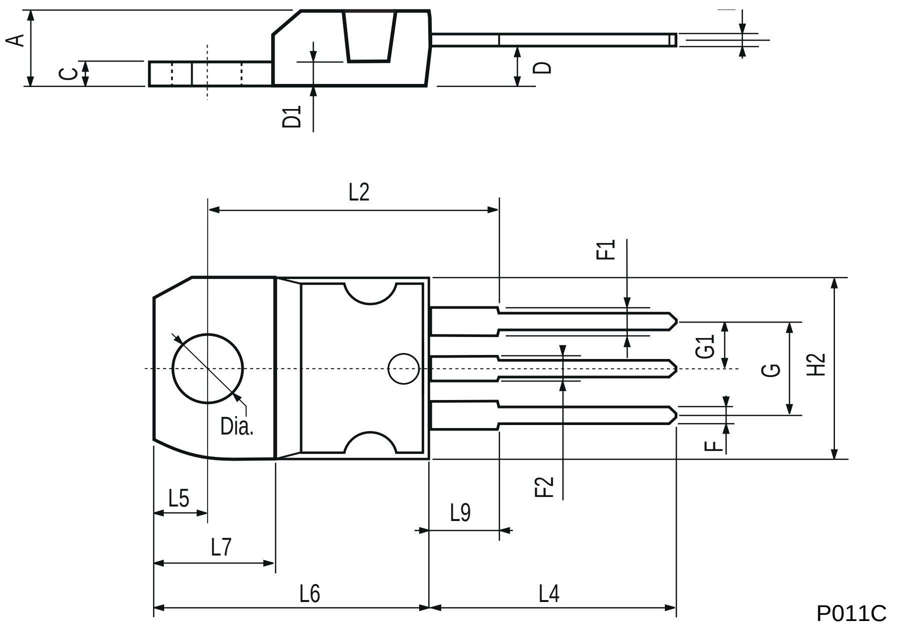


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



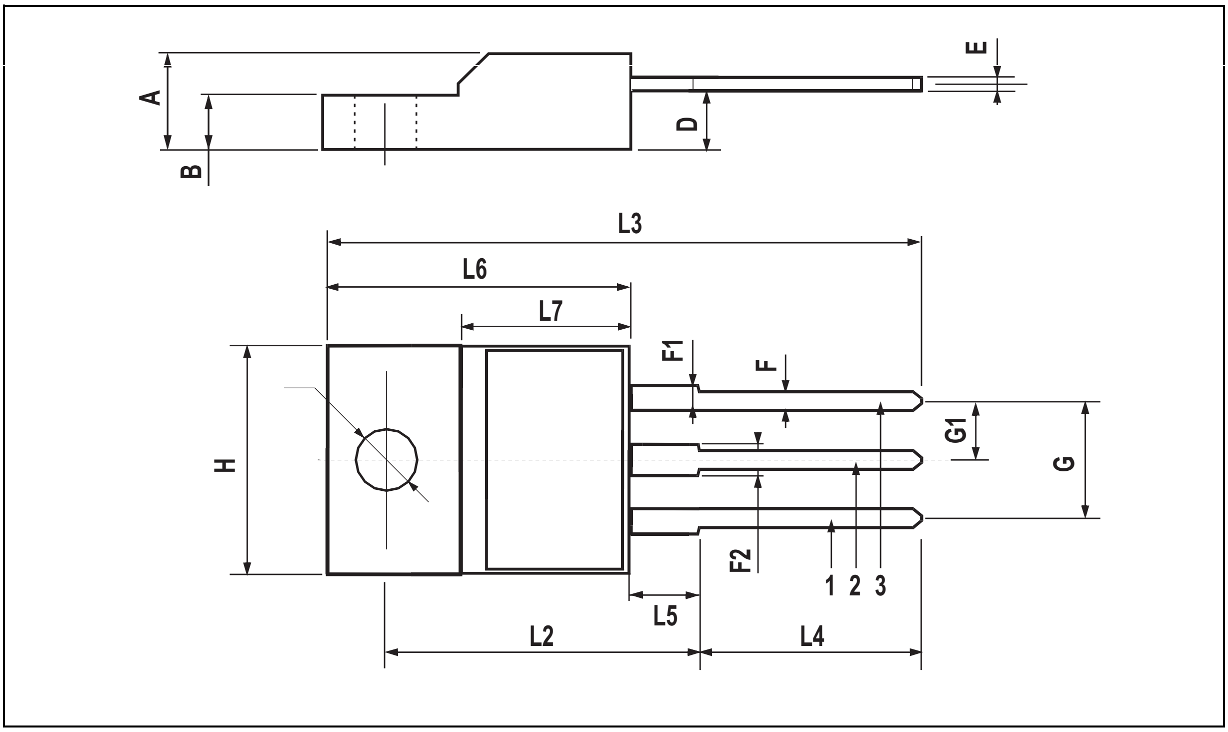
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.5	0.045		0.067
F2	1.15		1.5	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118